Signature and Name of Invigilator	Answer Sneet No.:								
4 (0)	(To be filled by the Candidate)								
1. (Signature)	Roll No.								
(Name)	(In figures as per admission card)								
2. (Signature)	Roll No.								
	(In words)								
(Name)	,								
1 9906	Test Booklet No.								
J-8806	APER – II								
Time: 1 <sup>1</sup> / <sub>4</sub> hours] ELECTRO	ONIC SCIENCE [Maximum Marks : 100								
Number of Pages in this Booklet : 12	Number of Questions in this Booklet : 50								
Instructions for the Candidates	परीक्षार्थियों के लिए निर्देश								
1. Write your roll number in the space provided on the top of	of this 1. पहले पृष्ठ के ऊपर नियत स्थान पर अपना रोल नम्बर लिखिए।								
page.	2. इस प्रश्न-पत्र में पचास बहुविकल्पीय प्रश्न हैं।								
2. This paper consists of fifty multiple-choice type of question									
<ol><li>At the commencement of examination, the question bo will be given to you. In the first 5 minutes, you are reque</li></ol>									
to open the booklet and compulsorily examine it as belo									
(i) To have access to the Question Booklet, tear off the p	paper सील को फाड लें। खुली हुई या बिना स्टीकर-सील की पुस्तिका								
seal on the edge of this cover page. Do not acc booklet without sticker-seal and do not accept an	open (Mark 1 47)								
booklet.	(ii) कवर पृष्ठ पर छपे निर्देशानुसार प्रश्न-पुस्तिका के पृष्ठ तथा प्रश्नों की								
(ii) Tally the number of pages and number of question									
the booklet with the information printed on the opage. Faulty booklets due to pages/questions mis									
or duplicate or not in serial order or any o	other उसी समय उसे लौटाकर उसके स्थान पर दूसरी सही प्रश्न-पुस्तिका								
discrepancy should be got replaced immediately correct booklet from the invigilator within the peri									
5 minutes. Afterwards, neither the question bo									
will be replaced nor any extra time will be given.	· · · · · · · · · · · · · · · · · · ·								
(iii) After this verification is over, the Serial No. of the bo should be entered in the Answer-sheets and the S	Serial करें और उत्तर-पत्रक की क्रम संख्या इस प्रश्न-पुस्तिका पर अंकित कर								
No. of Answer Sheet should be entered on this Boo	l N								

Example: A B D where (C) is the correct response.

correct response against each item.

Your responses to the items are to be indicated in the Answer Sheet given inside the Paper I booklet only. If you mark at any place other than in the ovals in the Answer Sheet, it will not be evaluated.

Each item has four alternative responses marked (A), (B), (C) and (D). You have to darken the oval as indicated below on the

- 6. Read instructions given inside carefully.
- 7. Rough Work is to be done in the end of this booklet.
- If you write your name or put any mark on any part of the test booklet, except for the space allotted for the relevant entries, which may disclose your identity, you will render yourself liable to disqualification.
- 9. You have to return the test question booklet to the invigilators at the end of the examination compulsorily and must not carry it with you outside the Examination Hall.
- 10. Use only Blue/Black Ball point pen.
- 11. Use of any calculator or log table etc., is prohibited.
- 12. There is NO negative marking.

5. प्रश्नों के उत्तर **केवल प्रश्न पत्र I के अन्दर दिये गये** उत्तर-पत्रक पर ही अंकित करने हैं। यदि आप उत्तर पत्रक पर दिये गये दीर्घवृत्त के अलावा किसी अन्य स्थान पर उत्तर चिन्हांकित करते है, तो उसका मूल्यांकन नहीं होगा।

4. प्रत्येक प्रश्न के लिए चार उत्तर विकल्प (A), (B), (C) तथा (D) दिये गये हैं।

आपको सही उत्तर के दीर्घवृत्त को पेन से भरकर काला करना है जैसा कि नीचे

- 6. अन्दर दिये गये निर्देशों को ध्यानपूर्वक पढें।

दिखाया गया है।

जबकि (C) सही उत्तर है।

7. कच्चा काम (Rough Work) इस पुस्तिका के अन्तिम पृष्ठ पर करें।

उदाहरण : A B D

- यदि आप उत्तर-पुस्तिका पर अपना नाम या ऐसा कोई भी निशान जिससे आपकी पहचान हो सके, किसी भी भाग पर दर्शाते या अंकित करते हैं तो परीक्षा के लिये अयोग्य घोषित कर दिये जायेंगे।
- 9. आपको परीक्षा समाप्त होने पर उत्तर-पुस्तिका निरीक्षक महोदय को लौटाना आवश्यक है और परीक्षा समाप्ति के बाद अपने साथ परीक्षा भवन से बाहर न लेकर जायें।
- 10. केवल नीले / काले बाल प्वाईंट पैन का ही इस्तेमाल करें।
- 11. किसी भी प्रकार का संगणक ( कैलकुलेटर ) या लाग टेबल आदि का प्रयोग वर्जित है।
- 12. गलत उत्तर के लिए अंक नहीं काटे जायेंगे।

## **ELECTRONIC SCIENCE**

## PAPER-II

**Note:** This paper contains **fifty** (50) objective-type questions, each question carrying **two** (2) marks. Attempt **all** of them.

In a semiconductor, if the charge carriers can make a transition from the valence to the conduction band without the change in the momentum value, the material is known

	as:										
	(A)	Wide band gap	material	(B)	Nar	row band gaj	p material				
	(C)	Direct band gap	material	(D)	D) Indirect band gap material						
2.	Whi	ch of the followin	g transisto	rs can be 11	sed in	a E - mode ?					
	(A)	JFET	O	SFET	(C)		istor	(D)	UJT		
3.	Tho	transient current	in loss from	I Coirce	iit who	on avaited free	m an ac co	11rco i	c •		
Э.	(A)	an under damp		(B)		andamped	iii aii ac so	urce i	э.		
	(C)	an over damped		(D)		cally damped	1				
	(C)	an over damped	1	(D)	CII	carry damped	L				
4.	The	Thevinis theorem	results in	:							
	(A)	a voltage source	with an ir	mpedance i	n serie	:S					
	(B)	a voltage source	with an i	mpedance i	in para	llel					
	(C)	a current source	with an i	mpedance i	n serie	es.					
	(D)	a current source	e with an i	mpedance :	in para	ıllel					
5.	The	voltage gain in th	e inverting	2 OPAMP i	s :						
•	(A)	ratio of feedback	_	-							
	(B)	ratio of output	-			nce					
	(C)	ratio of input in	_	<del>-</del>	_						
	(D)	reverse ratio of	_	=	1						
6.	IEET	Thas main drawb	ack of								
0.	(A)	having low inp		nce (B)	have	ing high outp	out impode	nco			
	(A) (C)	being noisy	at iiripedai	(D)		ing mgn outp ing small gair	-		roduct		
	(C)	being noisy		(D)	i ilav.	ing sinan gan	.i - Danawi	um p	Toduct		
7.	The	minimum numbe	r of flip - f	lops requir	ed in a	counter to co	ount 60 pul	ses is	:		
	(A)	4	(B) 6		(C)	8	(D)	10			
8.		CMOS logic fam lition :	ily, the po	wer consui	mption	will be lowe	est under t	he op	erating		
	(A)	$V_{DD} = 5V$ , $f_{max} =$	=1 MHz	(B)	$V_{DD}$	$_{0}$ = 5V, $f_{max}$ =	10 KHz				
		$V_{DD} = 10V$ , $f_{max}$				$_{0} = 10V, f_{max} =$					

1.

9.		ch of the followin ROM	g is ar (B)	n example o Hard Disk		tile m (C)	emory ? RAM	(D)	PROM
10.	If ins (A)	struction RST - 5 is 0020 H	s writte (B)	en in a prog 0024 H	ram, t	the pro	ogram control wi 0028 H	ill jump (D)	
11.	FOR (A) (C)	TRAN subroutine follows data car jumps main pro	d	ys:	(B) (D)		ws main prograi eeds main progr		
12.		structured progra WHILE - DO IF - THEN - ELS		g forbids us	se of : (B) (D)	DO - GO -	WHILE TO		
13.	The g	gain of an isotrop 0 dB	oic anto (B)	enna is : 5 dB		(C)	10 dB	(D)	15 dB
14.	valle	ording to energy by is separated by $e_g = \delta E_g$	an en	ergy of δE f	rom a	lowe		in wh	
15.	The l (A) (C)	PPM can be conv Monostable mul Bistable multivil	tivibra	· ·	y mod (B) (D)	Asta	g the circuit of : ble multivibrator he above	r	
16.	At hi (A) (C)	igher frequencies, Shot noise Flicker noise	the m	nost importa	ant typ (B) (D)	Tran	noise observed is sit time noise mal noise	S:	
17.	In a (A) (C)	thyristor holding more than latch equal to latching	ing cu	rrent	(B) (D)		than latching cu small	rrent	
18.	The f (A) (C)	following process Ion exchange Epitaxy	is use	ed to make o	optical (B) (D)	Titar	e guides : nium diffusion o lithography		
19.		icrophone is class Optical	sified (B)				lucer. Magnetic	(D)	Thermal
20.	Nyqu (A) (C)	uist stability criter Arguments S - plane	rion is	based on p	rincip (B) (D)	Imag	inary numbers ugates		

List - I	21.			t - I w	vith Li	st - II	and s	elect t	the co	rrect answer using the codes given below			
(a) lonic (b) Covalent (ii) Copper (c) Metallic (iii) Cipper (c) Metallic (iii) Silicon (d) Vander wall (iv) Sodium chloride (d) Vander wall (iv) Sodium chloride (e) Codes : (a) (b) (c) (d) (A) (iii) (iv) (ii) (ii) (B) (iv) (iii) (ii) (C) (iii) (iv) (ii) (ii) (D) (iv) (iii) (iii) (iii) (D) (iv) (ii) (iii) (iii) (D) (iv) (ii) (iii) (D) (iv) (ii) (iii) (D) (iv) (ii) (iii) (iv) (c) (c) (iv) (i) (ii) (iv) (c) (c) (d) (A) (iv) (iii) (iv) (c) (d) (A) (iv) (iii) (iv) (c) (d) (A) Attenuation constant (iv) (iv) (iv) (iv) (iv) (iv) (iv) (iv)		the list:						Tial	T				
(b) Covalent (c) Metallic (iii) Silicon (d) Vander wall (iv) Sodium chloride $Codes:$ (a) (b) (c) (d) (A) (iii) (iv) (ii) (i) (B) (iv) (iii) (i) (ii) (C) (iii) (iv) (i) (ii) (D) (iv) (iii) (ii) (C) (iii) (iv) (i) (ii) (D) (iv) (iii) (ii) (D) (iii) (D) (iii) (iii) (D) (ii) (ii		(2)					( <del>;</del> )			nn			
(c) Metallic (d) Vander wall (iv) Sodium chloride Codes: (a) (b) (c) (d) (A) (iii) (iv) (ii) (i) (B) (iv) (iii) (i) (i) (C) (iii) (iv) (ii) (i) (D) (iv) (iii) (i) (i) (D) (iv) (iii) (ii) (D) (iv) (iii) (ii) (D) (iv) (iii) (ii) (D) (iv) (iii) (ii) (D) (iv) (iii) (iii) (D) (i) (iv) (iii) (iii) (D) (c) (iv) (i) (iii) (iii) (D) (c) (iv) (i) (iii) (iiii) (iii) (iiii) (iii) (iii) (iiii) (iiii) (iii) (iiii) (iiii) (iiii) (iiii) (iii) (iiii) (iiii		` '							_	OII			
(d) Vander wall (iv) Sodium chloride $Codes:$ (a) (b) (c) (d) (A) (iii) (iv) (ii) (i) (B) (iv) (iii) (i) (ii) (C) (iii) (iv) (i) (ii) (D) (iv) (iii) (ii) (i) (D) (iv) (iii) (ii) (ii) (D) (iv) (iii) (ii) (ii) (D) (ii) (iii) (D) (ii) (ii		` '					, ,		-				
$ \begin{array}{c} \textit{Codes}: & \textbf{(a)} & \textbf{(b)} & \textbf{(c)} & \textbf{(d)} \\ & (A) & (iii) & (iv) & (ii) & (i) \\ & (B) & (iv) & (iii) & (i) & (ii) \\ & (C) & (iii) & (iv) & (i) & (ii) \\ & (D) & (iv) & (iii) & (i) & (i) \\ & (D) & (iv) & (iii) & (i) & (i) \\ & (D) & (iv) & (iii) & (i) & (i) \\ & (D) & (iv) & (iii) & (i) & (i) \\ & (D) & (iv) & (iii) & (i) & (i) \\ & (D) & (iv) & (iii) & (ii) \\ & (D) & ($					· a 11		` '			alarida			
$(A) \   (iii) \   (iv) \   (ii) \   (i) \   (B) \   (iv) \   (iii) \   (i) \   (ii) \   (C) \   (iii) \   (iv) \   (ii) \   (D) \   (iv) \   (iii) \   (ii) \   (D) \   (iv) \   (iii) \   (iii) \   (D) \   (iv) \   (iiii) \   (D) \   (iv) \   (iiii) \   (D) \   (iv) \   (D) \  $		` '				(c)	` '	<i>3</i> 001	uiii Ci	morrae			
(B) (iv) (iii) (i) (ii) (ii) (C) (iii) (iv) (i) (ii) (D) (iv) (iii) (iv) (i) (ii) (D) (iv) (iii) (ii) (i) (D) (iv) (iii) (ii) (ii) (D) (iv) (iii) (iii) (D) (iv) (iiii) (iii) (D) (D) (D) (D) (D) (D) (D) (D) (D) (D		Con											
(C) (iii) (iv) (ii) (ii) (ii) (D) (iv) (iii) (iii) (D) (iv) (iii) (iii) (D) (iv) (iii) (iii) (D) (iv) (D) (D) (D) (D) (D) (D) (D) (D) (D) (D			, ,										
22. Match List - I with List - II :  List - I  (a) Passive Network  (b) Active Network  (c) Lumped Network  (d) Distributed Network  (e) Contains electrically inseparable passive circuments  (f) Contains circuit elements without energy sources  (g) Distributed Network  (g) Contains circuit elements without energy sources  (g) Contains circuit elements without energy sources  (g) Contains circuit elements with energy sources  (g) (h) (c) (d)  (g) (ii) (iii) (iii)  (g) (iii) (iii) (iii)  (g) (iii) (iii) (iii)  (g) Velocity of wave propagation  (g) Skin depth  (g) Attenuation constant  (h) Velocity of wave propagation  (iv) $\frac{1}{\sqrt{\mu \epsilon}}$ (d) Attenuation constant  The correct matching is:  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (ii)  (B) (i) (iii) (iii) (iv)  (C) (iii) (iv) (i) (ii)			' '		1 1								
List - I  (a) Passive Network  (b) Active Network  (c) Lumped Network  (d) Distributed Network  (e) Contains electrically inseparable passive circulelements  (c) Lumped Network  (d) Distributed Network  (ii) Contains electrically inseparable passive circulelements  (c) Lumped Network  (iii) Contains circuit elements without energy sources  (d) Distributed Network  (iv) Contains circuit elements with energy sources  (d) Contains circuit elements with energy sources  (a) (b) (c) (d)  (A) (iii) (iv) (i) (ii)  (B) (i) (ii) (iii) (iv)  (C) (iv) (i) (ii) (iii)  (D) (i) (iv) (iii) (iii)  (D) (i) (iv) (iii) (iii)  (D) (i) (iv) (iii) (iii)  (a) Intrinsic Impedance  (b) Velocity of wave propagation  (c) Skin depth  (ii) $\frac{1}{\sqrt{\pi f \mu \sigma}}$ (d) Attenuation constant  The correct matching is:  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (ii)  (B) (i) (iii) (iii) (iv)  (C) (iiii) (iv) (i) (iii)			, ,	, ,	, ,								
List - I  (a) Passive Network  (b) Active Network  (c) Lumped Network  (d) Distributed Network  (e) Contains electrically inseparable passive circulelements  (c) Lumped Network  (d) Distributed Network  (ii) Contains electrically inseparable passive circulelements  (c) Lumped Network  (iii) Contains circuit elements without energy sources  (d) Distributed Network  (iv) Contains circuit elements with energy sources  (d) Contains circuit elements with energy sources  (a) (b) (c) (d)  (A) (iii) (iv) (i) (ii)  (B) (i) (ii) (iii) (iv)  (C) (iv) (i) (ii) (iii)  (D) (i) (iv) (iii) (iii)  (D) (i) (iv) (iii) (iii)  (D) (i) (iv) (iii) (iii)  (a) Intrinsic Impedance  (b) Velocity of wave propagation  (c) Skin depth  (ii) $\frac{1}{\sqrt{\pi f \mu \sigma}}$ (d) Attenuation constant  The correct matching is:  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (ii)  (B) (i) (iii) (iii) (iv)  (C) (iiii) (iv) (i) (iii)	22.	Mato	ch Lis	t - I w	rith Li	st - II	:						
(a) Passive Network (i) Contain electrically separable passive circuelements (b) Active Network (ii) Contains electrically inseparable passive circuelements (c) Lumped Network (iii) Contains circuit elements without energy sources (d) Distributed Network (iv) Contains circuit elements without energy sources (d) Distributed Network (iv) Contains circuit elements with energy sources (d) (A) (iii) (iv) (i) (ii) (iii) (B) (i) (iii) (iv) (i) (iii) (iii) (D) (i) (iv) (iv) (iv) (D) (iv) (D) (D) (D) (D) (D) (D) (D) (D) (D) (D								List	- II				
elements  (b) Active Network  (ii) Contains electrically inseparable passive circule elements  (c) Lumped Network  (iii) Contains electrically inseparable passive circule elements  (iv) Contains circuit elements without energy sources  (d) Distributed Network  (iv) Contains circuit elements with energy sources  (d) Distributed Network  (iv) Contains circuit elements with energy source of the correct matching is:  (a) (b) (c) (d)  (A) (iii) (ii) (iii) (iv)  (C) (iv) (i) (ii) (iii)  (D) (i) (iv) (iii) (iii)  23. Match List - I with List - II:  List - II  (a) Intrinsic Impedance  (b) Velocity of wave propagation  (c) Skin depth  (ii) $\sqrt{\mu/\epsilon}$ (d) Attenuation constant  The correct matching is:  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (i)  (B) (i) (iii) (ii) (iv)  (C) (iii) (iv) (i) (iii)		(a)			etwor	k				ain electrically separable passive circuit			
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The correct matching is :  (a) (b) (c) (d)  (A) (iii) (iv) (i) (ii)  (B) (i) (ii) (iii) (iv)  (C) (iv) (i) (ii) (iii)  (D) (i) (iv) (iii) (ii)  23. Match List - I with List - II :  List - I  (a) Intrinsic Impedance  (i) $\frac{1}{\sqrt{\pi} f \mu \sigma}$ (b) Velocity of wave propagation  (ii) $\sqrt{\omega \mu \sigma}$ (c) Skin depth  (iii) $\sqrt{\mu/\epsilon}$ (d) Attenuation constant  (iv) $\frac{1}{\sqrt{\mu \epsilon}}$ The correct matching is :  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (i)  (B) (i) (iii) (iii) (iv)  (C) (iiii) (iv) (i) (iii)		(c) Lumped Network					(iii)						
The correct matching is :  (a) (b) (c) (d)  (A) (iii) (iv) (i) (ii)  (B) (i) (ii) (iii) (iv)  (C) (iv) (i) (ii) (iii)  (D) (i) (iv) (iii) (ii)  23. Match List - I with List - II :  List - I  (a) Intrinsic Impedance  (i) $\frac{1}{\sqrt{\pi} f \mu \sigma}$ (b) Velocity of wave propagation  (ii) $\sqrt{\omega \mu \sigma}$ (c) Skin depth  (iii) $\sqrt{\mu/\epsilon}$ (d) Attenuation constant  (iv) $\frac{1}{\sqrt{\mu \epsilon}}$ The correct matching is :  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (i)  (B) (i) (iii) (iii) (iv)  (C) (iiii) (iv) (i) (iii)		(d) Distributed Network				(iv)	ains circuit elements with energy sources						
(a) (b) (c) (d) (A) (iii) (iv) (i) (ii) (B) (i) (ii) (iii) (iv) (C) (iv) (i) (ii) (iii) (D) (i) (iv) (iii) (ii) (D) (i) (iv) (iii) (iii) (D) (i) (iv) (iii) (iii) (D) (i) (iv) (iii) (D) (iii) (D) (iii) (D) (D) (D) (D) (D) (D) (D) (D) (D) (D		` '	correc	t mat	ching	is:		` ,					
(B) (i) (ii) (iii) (iv) (iv) (C) (iv) (i) (ii) (iii) (D) (i) (iv) (iii) (iii) (D) (i) (iv) (iiii) (iii) (D) (i) (iv) (iiii) (iii) (D) (i) (iv) (iiii) (iii) (D) (iiii) (D) (iiiiiiiiii					_								
(B) (i) (ii) (iii) (iv) (C) (iv) (i) (ii) (iii) (D) (i) (iv) (iii) (iii) (D) (i) (iv) (iii) (iii) (D) (i) (iv) (iiii) (iii) (D) (i) (iv) (iiii) (D) (iiii) (D) (iiiiiiiiiiiiiii		(A)	(iii)	(iv)	(i)	(ii)							
(D) (i) (iv) (iii) (ii)  23. Match List - I with List - II:  List - I  (a) Intrinsic Impedance  (i) $\frac{1}{\sqrt{\pi} f \mu \sigma}$ (b) Velocity of wave propagation  (c) Skin depth  (ii) $\sqrt{\mu/\epsilon}$ (d) Attenuation constant  (iv) $\frac{1}{\sqrt{\mu \epsilon}}$ The correct matching is:  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (i)  (B) (i) (iii) (ii) (iv)  (C) (iii) (iv) (i) (ii)		(B)	(i)	(ii)	(iii)	(iv)							
23. Match List - I with List - II :  List - I  (a) Intrinsic Impedance  (i) $\frac{1}{\sqrt{\pi f \mu \sigma}}$ (b) Velocity of wave propagation  (c) Skin depth  (d) Attenuation constant  (ii) $\sqrt{\omega \mu \sigma}$ (iii) $\sqrt{\mu / \epsilon}$ (d) Attenuation constant  (iv) $\frac{1}{\sqrt{\mu \epsilon}}$ The correct matching is :  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (i)  (B) (i) (iii) (ii) (iv)  (C) (iii) (iv) (i) (ii)		(C)	(iv)	(i)	(ii)	(iii)							
List - I  (a) Intrinsic Impedance  (i) $\frac{1}{\sqrt{\pi} f \mu \sigma}$ (b) Velocity of wave propagation  (ii) $\sqrt{\omega \mu \sigma}$ (c) Skin depth  (iii) $\sqrt{\mu/\epsilon}$ (d) Attenuation constant  (iv) $\frac{1}{\sqrt{\mu \epsilon}}$ The correct matching is:  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (i)  (B) (i) (iii) (ii) (iv)  (C) (iii) (iv) (i) (ii)		(D)	(i)	(iv)	(iii)	(ii)							
(a) Intrinsic Impedance (i) $\frac{1}{\sqrt{\pi} f \mu \sigma}$ (b) Velocity of wave propagation (ii) $\sqrt{\omega \mu \sigma}$ (c) Skin depth (iii) $\sqrt{\mu/\epsilon}$ (d) Attenuation constant (iv) $\frac{1}{\sqrt{\mu \epsilon}}$ The correct matching is:  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (i)  (B) (i) (iii) (ii) (iv)  (C) (iii) (iv) (i) (ii)	23.	Mato			ith Li	st - II	:						
(b) Velocity of wave propagation (ii) $\sqrt{\omega\mu\sigma}$ (c) Skin depth (iii) $\sqrt{\mu/\epsilon}$ (d) Attenuation constant (iv) $\sqrt{\mu\epsilon}$ The correct matching is:  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (i)  (B) (i) (iii) (ii) (iv)  (C) (iii) (iv) (i) (iii)			List	- I						List - II			
(c) Skin depth (iii) $\sqrt{\mu/\epsilon}$ (d) Attenuation constant (iv) $\sqrt{1/\mu\epsilon}$ The correct matching is:  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (i)  (B) (i) (iii) (ii) (iv)  (C) (iii) (iv) (i) (ii)		(a)	Intri	nsic I	mped	ance			(i)	$\frac{1}{\sqrt{\pi f \mu \sigma}}$			
The correct matching is:  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (i)  (B) (i) (iii) (ii) (iv)  (C) (iii) (iv) (i) (ii)		(b) Velocity of wave propa				pagati	on	. ,					
The correct matching is:  (a) (b) (c) (d)  (A) (iv) (iii) (ii) (i)  (B) (i) (iii) (ii) (iv)  (C) (iii) (iv) (i) (ii)		(c)	Skin	deptl	h				(iii)	$\sqrt{\mu/\epsilon}$			
(a) (b) (c) (d) (A) (iv) (iii) (ii) (i) (B) (i) (iii) (ii) (iv) (C) (iii) (iv) (i) (ii)		(d)	Atte	nuatio	on coi	nstant			(iv)	$\frac{1}{\sqrt{\mu  \epsilon}}$			
(a) (b) (c) (d) (A) (iv) (iii) (ii) (i) (B) (i) (iii) (ii) (iv) (C) (iii) (iv) (i) (ii)		The	correc	t mat	ching	is:							
(A) (iv) (iii) (ii) (i) (B) (i) (iii) (ii) (iv) (C) (iii) (iv) (i) (ii)					_								
(B) (i) (iii) (ii) (iv) (C) (iii) (iv) (ii) (iii)		(A)		, ,									
(C) (iii) (iv) (i) (ii)		(B)	(i)	(iii)	. ,								
		(C)		(iv)									
		(D)	(ii)	(i)	(iii)	(iv)							

<b>24.</b> Match List - I with List - II:							
		List	- I				List - II
	(a)	Gun	n dioc	le		(i)	Junction less device
	(b)	Solar	cell			(ii)	Single Junction device
	(c) BJT					(iii)	Double Junction device
	(d)	SCR				(iv)	Triple Junction device
	The	correc	t mat	ching	is:		
		(a)	(b)	(c)	(d)		
	(A)	(i)	(ii)	(iii)	(iv)		
	(B)	(iii)	(iv)	(i)	(ii)		
	(C)	(i)	(iv)	(iii)	(ii)		
	(D)	(iii)	(ii)	(i)	(iv)		
25.	Mato	ch List	- I w	ith Lis	st - II :		
		List	- I				List - II
	(a)	8255	;			(i)	Programmable DMA controller
	(b)	8257	•			(ii)	Programmable Counter/Timer
	(c) 8259					(iii)	Programmable peripheral Interface
	(d)	8253	,			(iv)	Programmable Interrupt controller
	The	correc	t mat	ching	is:		
		(a)	(b)	(c)	(d)		
	(A)	(iii)	(iv)	(i)	(ii)		
	(B)	(iv)	(i)	(ii)	(iii)		
	(C)	(iii)	(i)	(iv)	(ii)		
	(D)	(iv)	(iii)	(ii)	(i)		
26.	Mato	ch List	- I w	ith Lis	st - II :		
		List	- I				List - II
	(a)	Float	t			(i)	1 byte
	(b)	Chai	r			(ii)	2 bytes
	(c)	Int				(iii)	10 bytes
	(d)	Long	g doul	ole		(iv)	4 bytes
	The	correc	t mat	ching	is:		
		(a)	(b)	(c)	(d)		
	(A)	(i)	(ii)	(iii)	(iv)		
	(B)	(ii)	(i)	(iv)	(iii)		
	(C)	(iv)	(ii)	(iii)	(i)		
	(D)	(iv)	(i)	(ii)	(iii)		

27.	Mato	ch Lis	t - I w	ith Lis	st - II :	:			
		List	- I				List	- II	
	(a)	F.M.	Broa	dcast				(i)	100 tetra hertz
	(b)	A.M	. Broa	dcast				(ii)	10 GHz
	(c)	Mici	owav	e Cor	nmun	icatio	n	(iii)	200 KHz
	(d)	Opti	ical C	ommu	ınicati	on		(iv)	600 MHz
	The	correc	ct mat	ching	is:				
		(a)	(b)	(c)	(d)				
	(A)	(iii)	(iv)	(ii)	(i)				
	(B)	(ii)	(i)	(iii)	(iv)				
	(C)	(iii)	(ii)	(iv)	(i)				
	(D)	(iv)	(iii)	(ii)	(i)				
28.	Mato	ch Lis	t - I w	ith Lis	st - II :	:			
		List	- I						List - II
	(a)	Idea	1 OPA	MP				(i)	Increased bandwidth
	(b)	Push	n pull	ampli	fier			(ii)	Infinite input impedance
	(c)		-	-	ick am	nplifie	r	(iii)	Increased gain
	(d)	_			k amp	_		(iv)	Power amplification
	The	correc	ct mat	ching	is:				•
		(a)	(b)	(c)	(d)				
	(A)	(i)	(iii)	(ii)	(iv)				
	(B)	(ii)	(iv)	(i)	(iii)				
	(C)	(iv)	(i)	(iii)	(ii)				
	(D)	(iii)	(i)	(ii)	(iv)				
29.	Mato	ch Lis	t - I w	ith Lis	st - II :	:			
		List	- I				List	- II	
	(a)	DC -	- DC			(i)	Inve	rters	
	(b)	DC -	- AC			(ii)	Cycl	oconv	rerters
	(c)	AC -	- DC			(iii)	Cho	ppers	
	(d)	AC -	- AC			(iv)	Rect	ifiers	
	The	correc	ct mat	ching	is:				
		(a)	(b)	(c)	(d)				
	(A)	(ii)	(iii)	(i)	(iv)				
	(B)	(i)	(iv)	(iii)	(ii)				
	(C)	(iii)	(iv)	(ii)	(i)				
	(D)	(iii)	(i)	(iv)	(ii)				

**30.** Match List - I with List - II:

#### List - I

- (a) Strain gauge
- (b) Eddy current gauge
- (c) Dielectric gauge
- (d) Piezo electric pick up

The correct matching is:

- (a) (b) (c) (d)
- (A) (iii) (ii) (iv) (i)
- (B) (ii) (iii) (i) (iv)
- (C) (iv) (iii) (ii) (i)
- (D) (iii) (i) (ii) (iv)

(Questions 31 to 40): The following items consist of two statements, one labelled the "Assertion (A)" and the other labelled the "Reason (R)". You are to examine these two statements carefully and decide if the Assertion (A) and the Reason (R) are individually true and if so, whether the Reason is a correct explanation of the Assertion. Select your answers to these items using the codes given below and mark your answer accordingly.

List - II

Voltage generating type

Variable inductance type

Variable capacitance type

Variable resistance type

(i)

(ii)

(iii)

(iv)

### Codes:

- (A) Both (A) and (R) are true and (R) is the correct explanation of (A)
- (B) Both (A) and (R) are true but (R) is not correct explanation of (A)
- (C) **(A)** is true but **(R)** is false
- (D) **(A)** is false but **(R)** is true
- **31. Assertion (A):** Tunnel diode can be used as a microwave oscillator.

**Reason (R):** The diode is made up of degenerate semiconductor.

**32. Assertion (A):** In a constant voltage source, the internal impedance of the voltage source is very low as compared to the load impedance.

**Reason (R):** The lesser the ratio of  $Z_i/Z_{L'}$  the better is the source as a constant voltage source.

**33. Assertion (A):** NPN transistors are generally used in amplifiers in CE mode.

**Reason (R):** The gain of an amplifier in CE mode is greater than common base mode.

**34. Assertion (A):** A half adder is faster than full adder.

**Reason (R):** A half adder gives only one output while a full adder gives two outputs.

**35. Assertion (A):** High level languages are third generation languages (3 GLs).

**Reason (R):** The program written in high level languages is problem oriented rather

than computer oriented.

**36. Assertion (A):** Mode 2 operation of 8255 is strobed bidirectional operation.

**Reason (R):** When Port A is programmed in mode 2, the Port B can be used in

either mode 1 or mode 0.

37. Assertion (A): Gunn diode is generally used to generate power at microwave

frequencies.

**Reason (R):** Gunn diode is made up of degenerate semiconductors.

**38. Assertion (A):** Radio and Television receivers are generally of the super heterodyne

type.

**Reason (R):** Wireless communication is possible by receiving signals through super

heterodyne receivers.

**39. Assertion (A):** Thyristors are preferred to power diodes in variable power rectifiers.

**Reason (R):** Thyristors provide controlled rectification and also the power loss in

them is less.

**40. Assertion (A):** The Wien Bridge can be used for frequency measurement.

**Reason (R):** The Wien Bridge uses only capacitors and resistors.

**41.** The below mentioned are the TTL - sub families.

- (i) 74
- (ii) 74 S
- (iii) 74 LS

The correct sequence of these sub families in the increasing order of their propagation delay in nano seconds is :

- (A) (ii), (i), (iii)
- (B) (i), (iii), (ii)
- (C) (iii), (i), (ii)
- (D) (i), (ii), (iii)

42.	The various processor chips which operate at different speeds are : (i) $8086$ (ii) $P - II$ (iii) $P - III$ (iv) $8085$ The correct sequence according to their speed of operation in increasing order is : (A) (i), (iii), (ii), (iv) (B) (iv), (ii), (i), (iii) (C) (iv), (i), (ii), (iii) (D) (i), (iv), (iii), (iii)
43.	In monolithic IC's, all the components are fabricated by:  (i) Oxidation  (ii) Epitaxial growth  (iii) Diffusion  (iv) Etching  The correct sequence of fabrication is:  (A) (i), (ii), (iii), (iv)  (B) (ii), (i), (iv), (iii)  (C) (iv), (iii), (ii), (i)  (D) (iii), (ii), (i), (iv)
44.	The following bands are used to identify the frequency rage from 1 GHz to 12 GHz:  (i) S  (ii) C  (iii) X  (iv) L  The correct sequence from lower frequency band to higher frequency band is:  (A) $(iv)$ , $(i)$ , $(ii)$ , $(iii)$ (B) $(i)$ , $(ii)$ , $(iii)$ , $(iv)$ (C) $(ii)$ , $(iv)$ , $(i)$ , $(iii)$ (D) $(iii)$ , $(iv)$ , $(ii)$ , $(ii)$
45.	Some oscillators used at various places in electronic circuits are:  (i) Hartley oscillator  (ii) Wein Bridge oscillator  (iii) Phase shift oscillator  (iv) Collpitts oscillator  The correct sequence of the above oscillators with respect to the range of frequencies that they generate is:  (A) (iii), (ii), (i), (iv)  (B) (iii), (i), (ii), (iv)  (C) (ii), (iii), (iv), (i)  (D) (iii), (ii), (iv), (i)

Read the passage below and answer the questions that follow based on your understanding of the passage:

In the era of increased global warming and diminishing fossil fuel supplies, we must begin to put a greater priority on harnessing alternative energy sources. Fortunately, there are a number of readily available, resources that are both cost effective and earth - friendly. Two such resources are solar power and geothermal power.

Solar energy, which reaches the earth through sunlight is so abundant that it could meet the needs of worldwide energy consumption 6,000 times more. And solar energy is easily harnessed through the use of photovoltaic cells that convert light into electricity. In the United States alone, more than 1,00,000 homes are equipped with solar electric systems in the form of solar panels consists solar cells generally made up of P - n junctions or solar roof tiles. And in other parts of the world, including many developing countries, the use of solar system is growing steadily.

Another alternative energy source, which is abundant in specific geographical areas, is geothermal power, which creates energy by tapping heat from below the surface of the earth. Hot water and steam that are tapped in underground pools are pumped to the surface and are used to run the generators, which produce electricity. Geothermal energy is 50,000 times more abundant than the entire known supply of fossil fuel resources. And as with solar power, the technology needed to utilise geothermal energy is fairly simple. A prime example of effective geothermal use is in Iceland, a region of high geothermal activity, where over 80% of private homes are provided with geothermal power.

Solar and geothermal energy are just two of a number of promising renewable alternatives to conventional energy sources. The time is long overdue to invest in the development and use of alternative energy on a global scale.

- **46.** Why should we consider to use alternative energy sources :
  - (A) Because fossil fuels are no longer available
  - (B) Because global warming has increased the amount of sunlight that reaches the earth
  - (C) Because they are free and available worldwide
  - (D) Because of conventional energy sources are being depleted and they cause environmental damage

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47.	Acco	ording to the passage, what can be inferred about solar roof tiles?
	(A)	They are used by many undeveloped countries
	(B)	They can convert geothermal power to electricity
	(C)	They are more expensive than solar panels
	(D)	They contain photovoltaic cell
48.	Dho	tovoltaic cells convert :
40.		
	(A)	Electric energy to light energy
	(B)	Magnetic energy to light energy
	(C)	Light energy to chemical energy
	(D)	Light energy to electric energy
49.	How	v is solar energy production similar to geothermal production?
	(A)	They both require the use of generators
	(B)	They both use heat from earth's surface
	(C)	They both require fairly simple technology
	(D)	They are both conventional and costly
50.	Solo	r electric systems are basically made up of :
30.		
	(A)	Silicon p - n junction diode
	(B)	Silicon
	(C)	Gallium Arsenide
	(D)	Indium phosphide hetrojunctions

# Space For Rough Work

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